High–voltage switching diode
RLS245

●Applications

High voltage switching

General purpose rectification

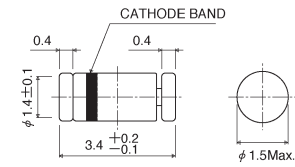
●Features

1) High reliability.
2) Small surface mounting type. (LLDS)
3) V_{RM} = 250V guaranteed.

●Construction

Silicon epitaxial planar

●External dimensions (Units: mm)



ROHM : LLDS
JEDEC : LL-34, SOD-80
Common : mini-MELF

●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	250	V
DC reverse voltage	V_R	220	V
Peak forward current	I_{FM}	625	mA
Mean rectifying current	I_O	200	mA
Surge current (1s)	I_{surge}	1000	mA
Power dissipation	P	300	mW
Junction temperature	T_j	175	℃
Storage temperature	T_{stg}	−65～+175	℃

Type	Color
RLS245	White

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	—	1.13	1.5	V	I_F=200mA
Reverse current	I_R	—	0.05	10	μA	V_R=220V
Capacitance between terminals	C_T	—	0.95	3	pF	V_R=0V, f=1MHz
Reverse recovery time	t_{rr}	—	—	75	ns	I_F=20mA, I_R=20mA, R_L=50Ω

●Electrical characteristic curves (Ta = 25°C unless specified otherwise)

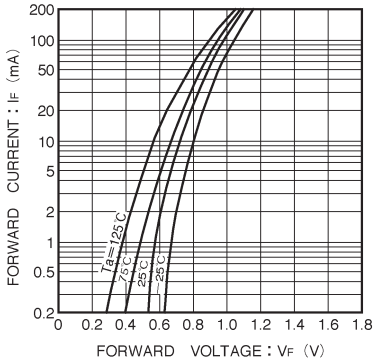


Fig. 1 Forward characteristics

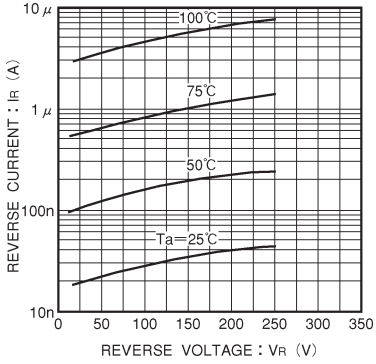


Fig. 2 Reverse characteristics

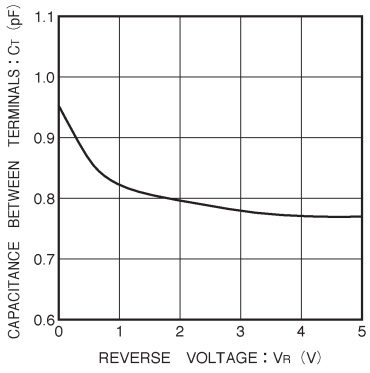


Fig. 3 Capacitance between terminals characteristics

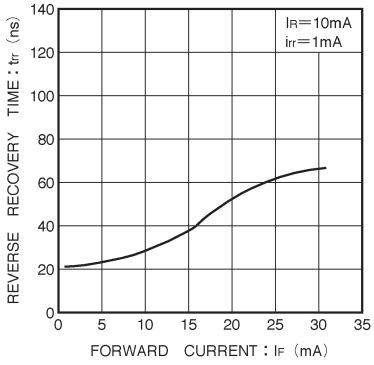


Fig. 4 Reverse recovery time characteristics

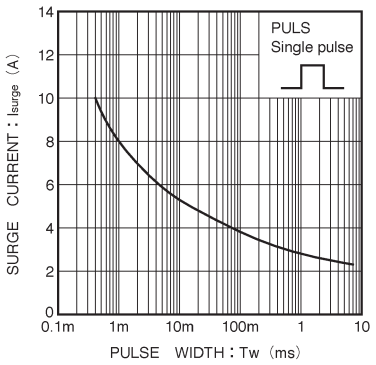


Fig. 5 Surge current characteristics

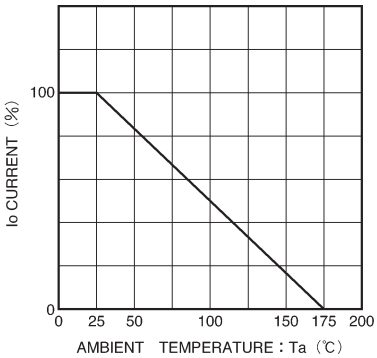


Fig. 6 Derating curve (mounting on glass epoxy PCBs)

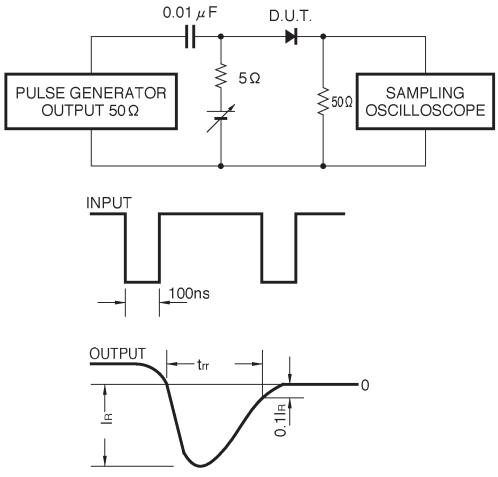


Fig. 7 Reverse recovery time (t_{rr}) measurement circuit